

## IN THE CLAIMS

Each claim of the present application is set forth below with a parenthetical notation immediately following the claim number indicating the current claim status. The Examiner's entry of the claim amendments, as shown in marked-up form, under Section 1.121 is respectfully requested.

1. (CURRENTLY AMENDED) A method for depositing material on a semiconductor wafer, wherein the wafer temperature is maintained within a temperature range, the method comprising:

providing a target comprising the material to be deposited;

supporting the wafer on a chuck, wherein the wafer is positioned between the target and the chuck;

depositing material from the target on the wafer in response to particles impinging the target; and

controlling the wafer temperature within the temperature range in response to heat flow from the chuck to the wafer. ~~by controlling the chuck temperature~~

2. (ORIGINAL) The method of claim 1 wherein the step of supporting the wafer further comprises supporting the wafer in a spaced apart relation from the chuck.

3. (ORIGINAL) The method of claim 1 wherein the wafer is thermally coupled to the chuck by radiant heat flow.

4. (CURRENTLY AMENDED) The method of claim 3 wherein the wafer temperature is substantially determined by the radiant heat flow from the chuck to the wafer.

5. (CURRENTLY AMENDED) The method of claim 1 further comprising positioning the wafer at a distance from the target such that the wafer temperature exhibits a greater dependence on a chuck temperature than on other parameters associated with the method for depositing material on the semiconductor wafer ~~chuck temperature substantially determines the wafer temperature~~.

6. (ORIGINAL) The method of claim 1 wherein the material comprises aluminum or an aluminum alloy.

7. (ORIGINAL) The method of claim 1 wherein the temperature range comprises temperatures between about 245° C and 285° C.

8. (ORIGINAL) The method of claim 1 wherein the step of controlling the wafer temperature comprises controlling the chuck temperature between about 350° C and 450° C.

9. (ORIGINAL) The method of claim 1 further comprising determining the wafer entry temperature prior to the step of depositing, wherein the step of controlling the wafer temperature further comprises controlling the chuck temperature in response to the wafer entry temperature.

10. (ORIGINAL) The method of claim 1 wherein the step of depositing further comprises depositing material with a <111> crystal orientation on the wafer.

11. (ORIGINAL) The method of claim 1 further comprising depositing an underlying layer on the wafer prior to depositing the material, wherein the underlying layer has a predetermined crystal orientation.

12. (ORIGINAL) The method of claim 11 wherein the underlying layer comprises titanium having a <002> crystal orientation.

13. (ORIGINAL) The method of claim 12 wherein the deposited material exhibits a desired grain orientation.

14. (ORIGINAL) The method of claim 1 wherein the step of positioning the wafer further comprises positioning the wafer at a distance of about 45 mm from the target.

15. (CURRENTLY AMENDED) A physical vapor deposition chamber for depositing material on a wafer, wherein the wafer temperature is maintained within a temperature range, comprising:

a target formed from the material to be deposited on the wafer;

a chuck for supporting the wafer;

a chuck heater; and

a controller for controlling the chuck heater such that the wafer temperature is maintained within the temperature range in response to heat flow from the chuck to the wafer.

16. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the wafer is heated by radiant heat flow from the chuck to the wafer.

17. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the wafer temperature is substantially determined by the chuck temperature.

18. (CURRENTLY AMENDED) The physical vapor deposition chamber of claim 15 wherein the wafer and the target are disposed in a spaced-apart relation to permit a chuck temperature, as controlled by the chuck heater, to substantially control the wafer temperature.

19. (ORIGINAL) The physical vapor deposition chamber of claim 18 wherein the spaced-apart relation comprises about 45 mm.

20. (ORIGINAL) The physical vapor deposition chamber of claim 15 further comprising a pedestal cover overlying the chuck, wherein the pedestal cover further comprises a plurality of pads on an upper surface thereof, and wherein the wafer is disposed on the plurality of pads.

21. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the material comprises aluminum or an aluminum alloy.

22. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the temperature range is between about 245° C and 285° C.

23. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the controller determines a chuck temperature in a range of between about 350° C and 450° C.

24. (ORIGINAL) The physical vapor deposition chamber of claim 15 further comprising a temperature measuring device for determining the wafer temperature, wherein the controller is responsive to the wafer temperature for controlling the chuck heater in response thereto.

25. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the deposited material has a substantially <111> crystal orientation.

26. (ORIGINAL) The physical vapor deposition chamber of claim 15 wherein the deposited material exhibits a desired grain orientation.